

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteri	Symbol	Value 30	Unit V		
Drain-Source Voltage				V _{DSS}	
Gate-Source Voltage			V _{GSS}	±25	V
Continuous Drain Current (Note 5) V _{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	ID	5.3 4.2	A
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	ID	8.0 6.3	A
Continuous Drain Current (Note 6) V _{GS} = 10V	$t \leq 10s$	T _A = +25°C T _A = +70°C	ID	9.5 7.7	A
Continuous Drain Current (Note 6) V _{GS} = 4.5V	Steady State	T _A = +25°C T _A = +70°C	ID	6.5 4.9	A
Continuous Drain Current (Note 6) V _{GS} = 4.5V	$t \leq 10s$	T _A = +25°C T _A = +70°C	ID	7.8 6.2	A
Pulsed Drain Current (Note 7)			I _{DM}	70	A
Avalanche Current (Notes 7 & 8)			I _{AR}	18	A
Repetitive Avalanche Energy (Notes 7 & 8) L = 0.1mH			E _{AR}	16	mJ

Thermal Characteristics

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 5)	PD	1.0	W
Thermal Resistance, Junction to Ambient $@T_A = +25^{\circ}C$ (Note 5)	R _{0JA}	130.6	°C/W
Power Dissipation (Note 6)	PD	2.07	W
Thermal Resistance, Junction to Ambient $@T_A = +25^{\circ}C$ (Note 6)	R _{0JA}	62.5	°C/W
Power Dissipation (Note 6) t ≤ 10s	PD	3.0	W
Thermal Resistance, Junction to Ambient $@T_A = +25^{\circ}C$ (Note 6) t \leq 10s	R _{0JA}	43.8	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C
Notes: 5. Device mounted on FR-4 PCB with minimum recommended pad layout, single si	ded.		

6. Device mounted on 2" x 2" FR-4 PCB with high coverage 2 oz. Copper, single sided.

7. Repetitive rating, pulse width limited by junction temperature.

8. I_{AR} and E_{AR} rating are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$.

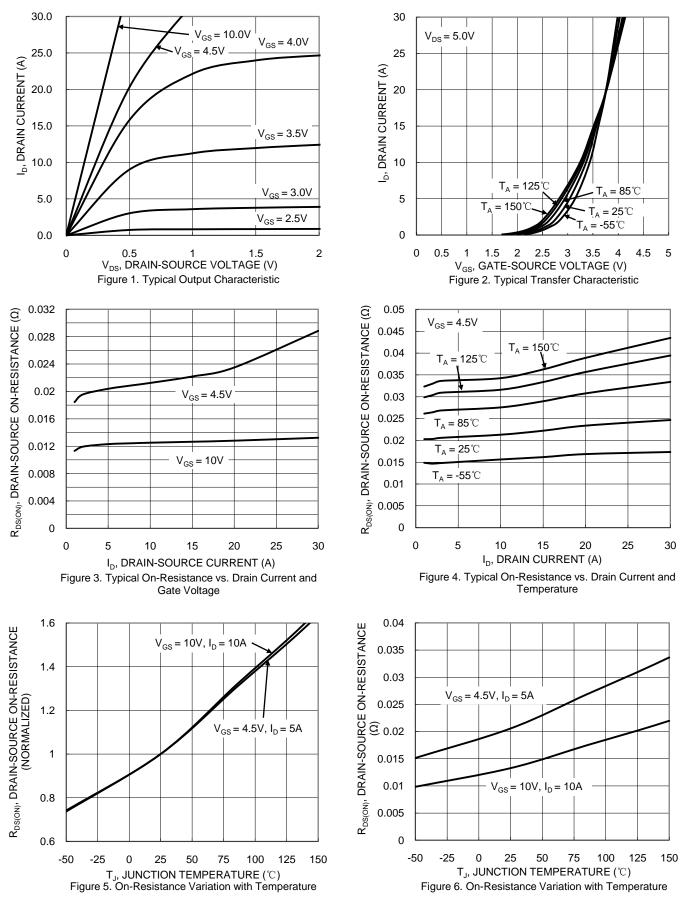
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Cumple of	Min	T	May	11	Test Condition	
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)		1					
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current $T_J = +25^{\circ}C$	IDSS	-	-	100	nA	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	-	-	±100	nA	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	0.9	1.2	1.8	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
Static Drain-Source On-Resistance		-	13.5	18.6	mΩ	$V_{GS} = 10V, I_D = 10A$	
	R _{DS(ON)}	-	22	26.5		$V_{GS} = 4.5V, I_D = 7.5A$	
Diode Forward Voltage	V _{SD}	-	0.7	1.0	V	$V_{GS} = 0V, I_S = 1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss	-	580	-			
Output Capacitance	Coss	-	110	-	pF	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	Crss	-	70	-			
Gate Resistance	Rg	-	2.0	3.0	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge V _{GS} = 4.5V	Qg	-	5.3	-		$V_{GS} = 4.5V, V_{DS} = 15V, I_D = 10A$ $V_{GS} = 10V, V_{DS} = 15V,$ $I_D = 10A$	
Total Gate Charge V _{GS} = 10V	Qg	-	11.3	-	nC		
Gate-Source Charge	Q _{gs}	-	1.9	-	no		
Gate-Drain Charge	Q _{gd}	-	1.9	-		ID = TOA	
Turn-On Delay Time	t _{D(ON)}	-	4.4	-	ns		
Turn-On Rise Time	t _R	-	4.6	-	ns	ns V _{GS} = 10V, V _{DS} = 15V,	
Turn-Off Delay Time	t _{D(OFF)}	-	19.5	-	$\frac{\text{ns}}{\text{ns}} R_{\text{L}} = 15\Omega, R_{\text{G}} = 6\Omega$		
Turn-Off Fall Time	t _F	-	5.8	-			

Notes: 9. Short duration pulse test used to minimize self-heating effect. 10. Guaranteed by design. Not subject to production testing.



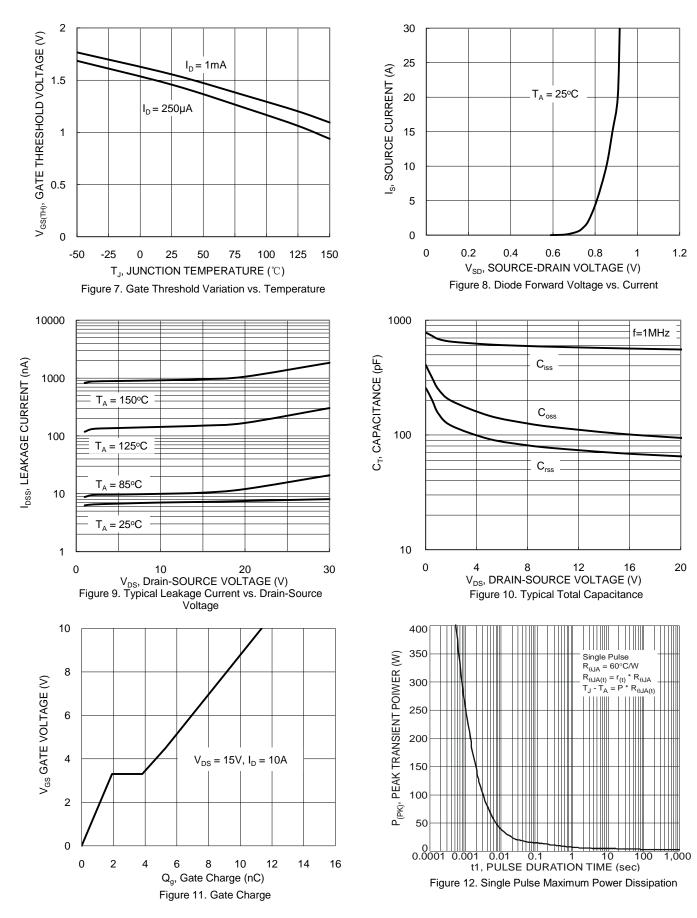
DMN3027LFG



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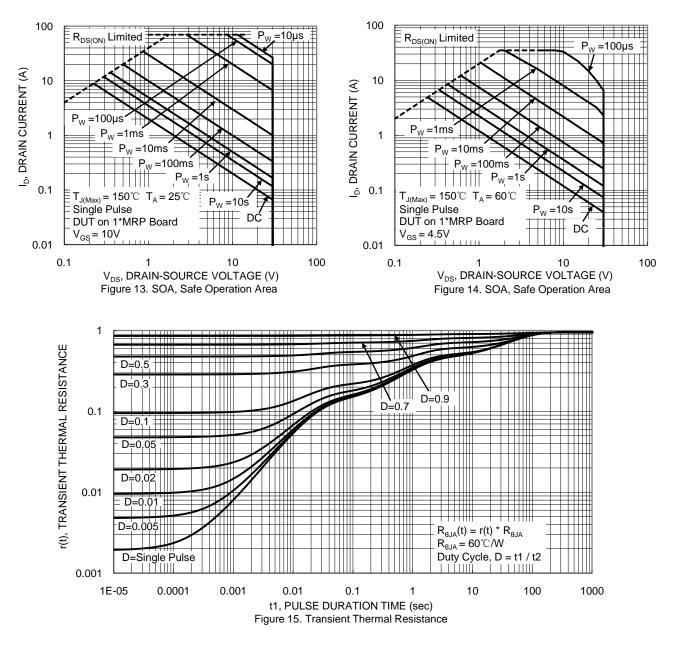


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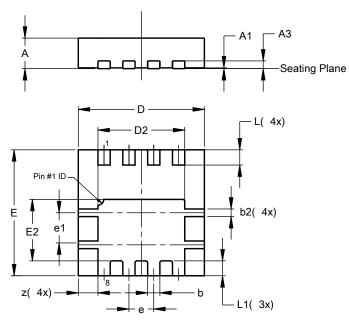
DMN3027LFG





Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



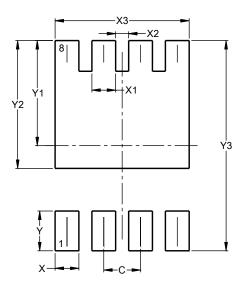
Р	POWERDI [®] 3333-8					
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05	0.02			
A3	-	-	0.203			
b	0.27	0.37	0.32			
b2	-	-	0.20			
D	3.25	3.35	3.30			
D2	2.22	2.32	2.27			
Е	3.25	3.35	3.30			
E2	1.56	1.66	1.61			
е	-	-	0.65			
e1	0.79	0.89	0.84			
L	0.35	0.45	0.40			
L1	_	_	0.39			
z	_	_	0.515			
All Dimensions in mm						

POWERDI[®]3333-8

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

POWERDI[®]3333-8



Dimensions	Value (in mm)		
C	0.650		
Х	0.420		
X1	0.420		
X2	0.230		
X3	2.370		
Y	0.700		
Y1	1.850		
Y2	2.250		
Y3	3.700		



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